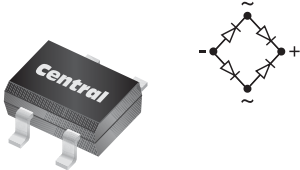


CBRHDSH1-100

SURFACE MOUNT
HIGH DENSITY
1 AMP SILICON
SCHOTTKY BRIDGE RECTIFIER

HD
BRIDGE



HD DIP CASE

DESCRIPTION:
The CENTRAL SEMICONDUCTOR CBRHDSH1-100 is a full wave bridge rectifier in a durable epoxy surface mount molded case, designed for low voltage full wave rectification applications. The molding compound used in this device has UL flammability classification 94V-O.

MARKING CODE: CSH110

FEATURES:

- Low Leakage Current (40nA TYP @ V_{RRM})
- Low Forward Voltage Drop Schottky Diodes
- High 1.0A Current Rating

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)			
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
DC Blocking Voltage	V_R	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	71	V
Average Forward Current	I_O	1.0	A
Peak Forward Surge Current	I_{FSM}	20	A
Power Dissipation	P_D	1.2	W
Operating Junction Temperature	T_J	-50 to +125	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	85	$^{\circ}\text{C/W}$

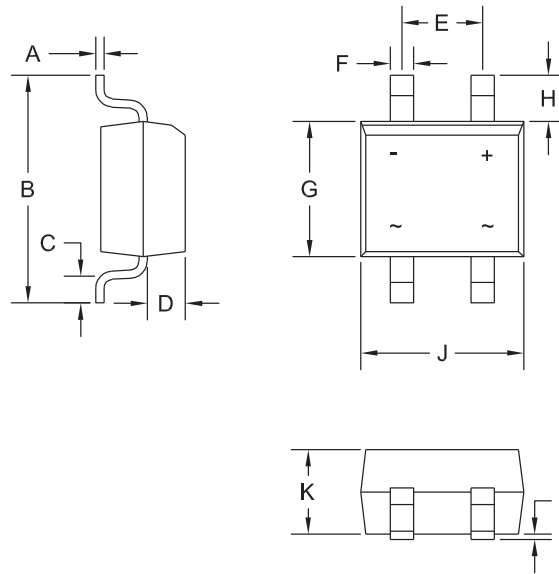
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)					
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=100\text{V}$		0.04	10	μA
I_R	$V_R=100\text{V}, T_A=50^{\circ}\text{C}$			1.0	mA
I_R	$V_R=100\text{V}, T_A=100^{\circ}\text{C}$			20	mA
BV_R	$I_R=150\mu\text{A}$	100			V
V_F	$I_F=500\text{mA}$		615	700	mV
V_F	$I_F=1.0\text{A}$		690	750	mV
C_J	$V_R=4.0\text{V}, f=1.0\text{MHz}$		230		pF

CBRHDSH1-100

SURFACE MOUNT
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HD DIP CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

HD DIP (REV: R2)

MARKING CODE: CSH110

R6 (22-May 2012)

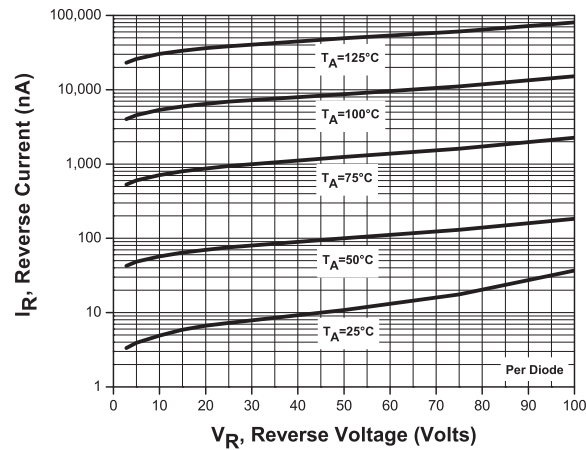
www.centalsemi.com

CBRHDSH1-100
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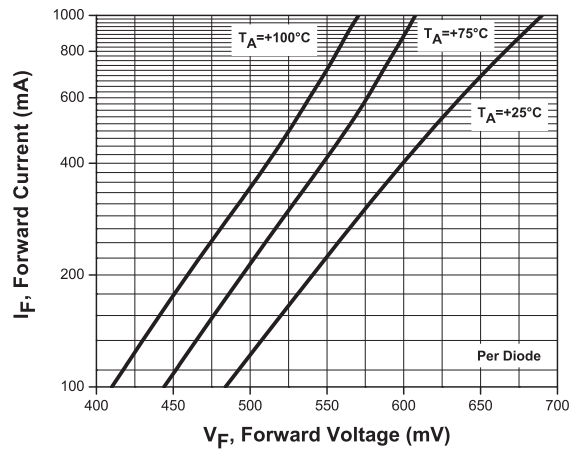


TYPICAL ELECTRICAL CHARACTERISTICS

Typical Leakage Current



Typical Forward Voltage



R6 (22-May 2012)

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OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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